MA6 and MA6/BA6 Contact Aligner Specifications

Exposure Optics:	UV400 Lamp	350 Watts

Spectral Lines (nanometers):

436	g-line
405	h-line
365	i-line
335	
313	

Intensity: 12 ± 0.1 mWatt/CM2
The aligners are set at a constant intensity.

Mask Size: 5 inch plate
Wafer Size: 4 inch; piece chuck is available for center placement of your piece underneath the mask.

Programs	**Description/Resolution**
Soft contact	A slight mechanical pressure is applied to produce contact. 2 μ line resolution
Hard Contact	Mechanical and Pneumatic pressure is applied to produce contact. 1 μ line resolution
Vacuum/LowVac	The contact between mask and wafer is optimized by evacuating the gap between the wafer and the mask. 0.8 μ line resolution
Proximity	A flag is placed between the mask and the wafer. Large features only >10 microns
Flood Exposure:	Available on MA6.
Alignment tolerance:	This depends on the program. photoresist, user experience, and wafer topography. On low vacuum or vacuum contact using a thin resist 0.5 μ alignment tolerance is achievable.